

High-reliability discrete products and engineering services since 1977

3N204-3N205

DUAL GATE MOSFET VHF AMPLIFIER

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Characteristic		Symbol	Min	Тур	Max	Unit
SMALL SIGNAL CHARACTERISTICS						
Forward transfer admittance ⁽³⁾						
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, V_{G1S} = 0, f = 1.0kHz)$	3N201, 3N202	Y _{fs}	8.0	12.8	20	mmhos
	3N203		7.0	12.5	15	
Input capacitance		C _{iss}				n.E
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_D = I_{DSS}, f = 1.0MHz)$		C _{iss}	-	3.3	-	pF
Reverse transfer capacitance $(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_D = 10mAdc, f = 1.0MHz)$		C _{rss}				,,r
			0.005	0.005 0.014	0.03	pF
Output capacitance	utput capacitance					pF
$(V_{DS} = 15Vdc, V_{G2S} = 4.0Vdc, I_{D} = I_{DSS}, f = 1.0MHz)$	C _{oss}	-	1.7	-		
FUNCTIONAL CHARACTERISTICS						
Noise figure						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	NF	-	1.8	4.5	dB
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		-	5.3	6.0	
Common source power gain						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	G_{ps}	15	20	25	dB
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		20	25	30	
$(V_{DD} = 18Vdc, f_{LO} = 245MHz, f_{RF} = 200MHz)$	3N202	G _c (5)	15	19	25	
Bandwidth						
$(V_{DD} = 18Vdc, V_{GG} = 7.0Vdc, f = 200MHz)$	3N201	B _w	5.0	-	9.0	MHz
$(V_{DD} = 18Vdc, f_{LO} = 245MHz, f_{RF} = 200MHz)$	3N202		4.5	-	7.5	
$(V_{DD} = 18Vdc, V_{GG} = 6.0Vdc, f = 45MHz)$	3N203		3.0	-	6.0	
Gain control gate-supply voltage (4)						
$(V_{DD} = 18Vdc, \Delta G_{ps} = -30dB, f = 200MHz)$	3N201	$V_{GG(GC)}$	0	-1.0	-3.0	Vdc
$(V_{DD} = 18Vdc, \Delta G_{ps} = -30dB, f = 45MHz)$	3N203		0	-0.6	-3.0	

ELECTRICAL CHARACTERISTICS (T_C = 25°C)

ELECTRICAL CHARACTERISTICS (T _C = 25 C)					
CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT	
OFF CHARACTERISTICS					
Drain-Source Breakdown Voltage	V.	25	_	Vdc	
$(I_D=10\mu A, V_{G1}=V_{G2}=-5.0V)$	V _{(BR)DSX}	25	-	Vuc	
Gate 1-Source Breakdown Voltage	V	+/-6	+/-30	Vdc	
(I _{G1} =+/- 10 mA) _{Note 1}	$V_{(BR)G1SO}$				
Gate 2-Source Breakdown Voltage	V	+/-6	+/-30	Vdc	
(I _{G2} =+/-10mA) _{Note 1}	V _{(BR)G2SO}	+/-0	+/-50	Vuc	
Gate 1 Leakage Current	I _{G1SS}	_	+/-10	nA	
$(V_{G1S}=+/-5.0V, V_{G2S}=V_{DS}=0)$		_	+/-10	IIA	
Gate 2 Leakage Current		-	+/-10	nA	
$(V_{G2S}=+/-5.0V, V_{G1S}=V_{DS}=0)$	I _{G2SS}				
Gate 1 to Source Cutoff Voltage	V	-0.5	-4.0	Vdc	
$(V_{DS}=15V, V_{G2S}=4.0V, I_D=20\mu A)$	V _{G1S(off)}				



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ELECTRICAL CHARACTERISTICS (T_C = 25°C)

CHARACTERISTIC	SYMBOL	MIN	MAX	UNIT		
Gate 2 to Source Cutoff Voltage (V_{DS} =15V, V_{G1S} =0V, I_D =20 μ A)	V _{G2S(off)}	-0.2	-4.0	Vdc		
ON CHARACTERISTICS						
Zero-Gate-Voltage Drain Current * (VDS=15V, VG2S=4.0V, VG1S=0V)	I _{DSS} *	6	30	mA		
SMALL SIGNAL CHARACTERISTICS						
Forward Transfer Admittance (VDS=15V, VGZS=4.0V, VGIS=0V, f=1.0kHz) Note 2	Y _{fs}	10	22	mmhos		
Input Capacitance (V_{DS} =15V, V_{G2S} =4.0V, I_D = I_{DSS} , f=1.0Mhz)	C _{iss}	TYP.3.0		pF		
Reverse Transfer Capacitance (V _{DS} =15V, V _{G2S} =4.0V, I _D =10mA, f=1.0MHz)	C _{rss}	0.005	0.03	pF		
Output Capacitance (V _{DS} =15V, V _{G2S} =4.0V, I _D =I _{DSS} , f=1.0MHz)	C _{oss}	TYP. 1.4		pF		
FUNCTIONAL CHARACTERISTICS	FUNCTIONAL CHARACTERISTICS					
Noise Figure (V _{DD} =18V, V _{GG} =7.0V, f=200MHz) 3N204 (V _{DS} =15V, V _{G2S} =4.0V, I _D =10mA, f=450MHZ) 3N204	NF		3.5 5.0	dB		
Common Source Power Gain (V _{DD} =18V, V _{GG} =7.0V, f=200MHz) 3N204 (V _{DS} =15V, V _{G2S} =4.0V, I _D =10mA, f=450MHz) 3N204	G _{ps}	20 14	28 -	dB		
Bandwidth (V _{DD} =18V, V _{GG} =7.0V, f=200MHz) 3N204 (V _{DD} =18V, f _{LC} =245MHz, f _{RF} =200MHz) _{Note 4} 3N205	BW	7.0 4.0	12 7.0	MHz		
Gain Control Gate Supply Voltage _(Note 3) (V _{DD} =18V, △GPS=300dB,f=200MHz) 3N204	V _{GG(GC)}	0	-2.0	Vdc		
Conversion Gain _(Note 4) (V _{DD} =18V, f _{LO} =245MHz, f _{RF} =200MHz) 3N205	G _(conv.)	17	28	dB		

^{*}PW=30 μ s, Duty Cycle \leq 2.0%.

¹⁾ All gate breakdown voltages are measured while the device is conducting rated gate current. This insures that the gate voltage limiting network is functioning properly.

²⁾ This parameter must be measured with bias voltages applied for less than five (5) seconds to avoid overheating.

³⁾ $\triangle G_{ps}$ is defined as the change in G_{ps} from the value at $V_{GG}\text{=}7.0V.$

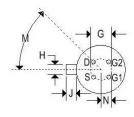
⁴⁾ Amplitude at input from local oscillator is 3 volts RMS.

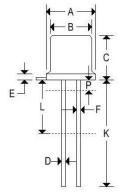


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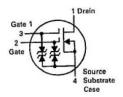
MECHANICAL CHARACTERISTICS

Case:	TO-72
Marking:	Body painted, alpha-numeric
Pin out:	See below





	TO-72				
	Inc	hes	Millimeters		
	Min	Max	Min	Max	
Α	150	0.230	-	5.840	
В	12	0.195	74)	4.950	
С	le.	0.210		5.330	
D	(+)	0.021	(-)	0.530	
E		0.030	-	0.760	
F	050	0.019	(5)	0.480	
G	0.100	BSC	2.540 BSC		
Н	-	0.046	-	1.170	
J	120	0.048	(4)	1.220	
K	0.500	=	12.700	-	
L	0.250	- 1	7-0	6.350	
M	45°	45° BSC		3SC	
N	0.050) BDC	1.270 BSC		
D	3927	0.050	750	1.270	



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